# Power MOSFET 30V, $72m\Omega$ , 3.5A, Single N-Channel

This low-profile high-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

#### **Features**

- Low On-Resistance
- 4V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mmt)

## **Typical Applications**

- Load Switch
- Battery Switch

#### **SPECIFICATIONS**

#### ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit	
Drain to Source Voltage	VDSS	30	٧	
Gate to Source Voltage	VGSS	±20	٧	
Drain Current (DC)	ID	3.5	Α	
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	14	А	
Power Dissipation When mounted on ceramic substrate (900mm² × 0.8mm)	PD	1	W	
Junction Temperature	Tj	150	°C	
Storage Temperature	Tstg	-55 to +150	°C	
Note 1: Stresses exceeding those listed in the Maximum Patings table may damage				

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit		
Junction to Ambient When mounted on ceramic substrate (900mm² × 0.8mm)	R <sub>θ</sub> JA	125	°C/W		

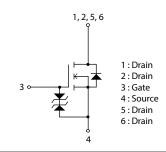


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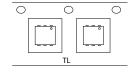
VDSS	R <sub>DS</sub> (on) Max	ID Max	
	72mΩ@ 10V		
30V	110mΩ@ 4.5V	3.5A	
	128mΩ@ 4V		

# ELECTRICAL CONNECTION N-Channel



#### **PACKING TYPE: TL**

### MARKING





#### **ORDERING INFORMATION**

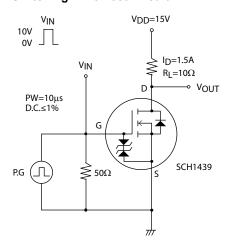
See detailed ordering and shipping information on page 5 of this data sheet.

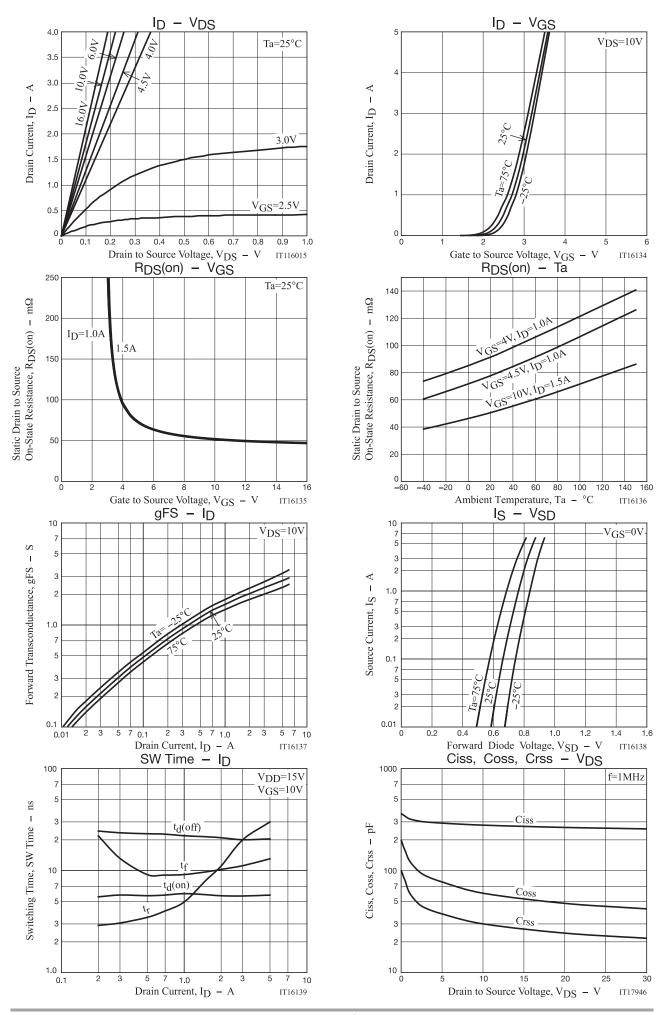
#### **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 2)

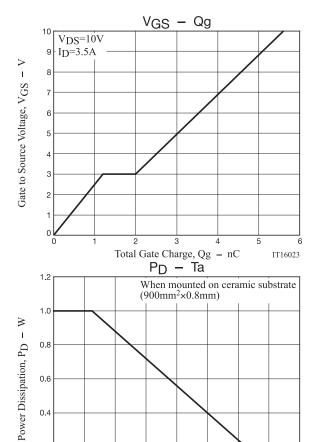
Parameter	Cumbal	0 1141		Value		
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μА
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μА
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transconductance	gFS	V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A		1.8		S
	R <sub>DS</sub> (on)1	I <sub>D</sub> =1.5A, V <sub>GS</sub> =10V		55	72	mΩ
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V		78	110	mΩ
Resistance	RDS(on)3	I <sub>D</sub> =1A, V <sub>GS</sub> =4V		91	128	mΩ
Input Capacitance	Ciss			280		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss			30		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			5.8		ns
Rise Time	t <sub>r</sub>	On a second of the district Observity		8.0		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		21		ns
Fall Time	tf			9.7		ns
Total Gate Charge	Qg			5.6		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A		1.2		nC
Gate to Drain "Miller" Charge	Qgd			0.8		nC
Forward Diode Voltage	V <sub>SD</sub>	IS=3.5A, VGS=0V		0.84	1.2	V

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **Switching Time Test Circuit**





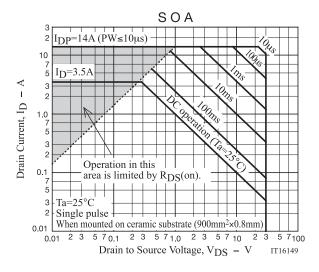


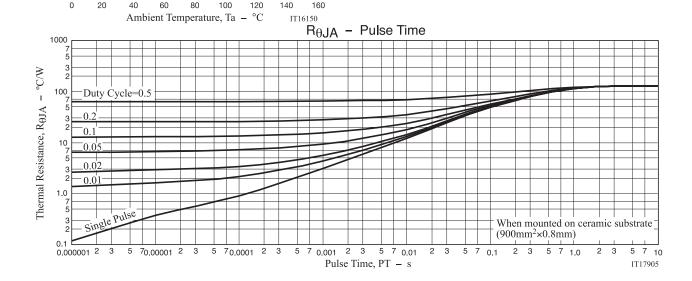
0.6

0.4

0.2

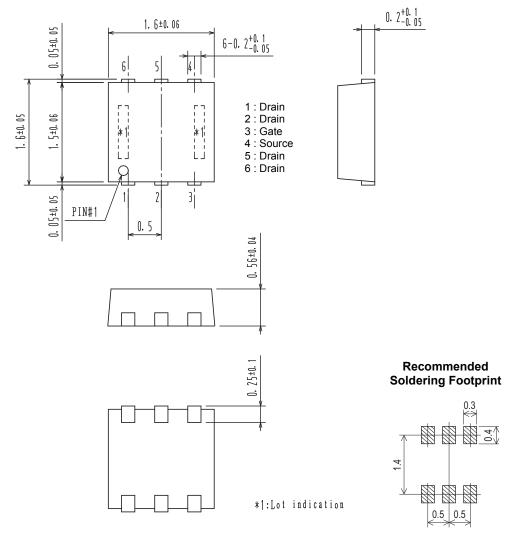
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#### PACKAGE DIMENSIONS

unit: mm SOT-563 / SCH6 CASE 463AB ISSUE O



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)	
SCH1439-TL-H	70	SOT-563 / SCH6	5,000 / Tape & Reel	
SCH1439-TL-W	ZQ	(Pb-Free / Halogen Free)		

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the SCH1439 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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